# 2N5457, 2N5458

## **JFETs - General Purpose**

### **N-Channel - Depletion**

N-Channel Junction Field Effect Transistors, depletion mode (Type A) designed for audio and switching applications.

#### **Features**

- N-Channel for Higher Gain
- Drain and Source Interchangeable
- High AC Input Impedance
- High DC Input Resistance
- Low Transfer and Input Capacitance
- Low Cross-Modulation and Intermodulation Distortion
- Plastic Encapsulated Package
- Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

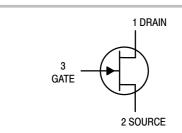
Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	Vdc
Drain – Gate Voltage	$V_{DG}$	25	Vdc
Reverse Gate - Source Voltage	V <sub>GSR</sub>	-25	Vdc
Gate Current	I <sub>G</sub>	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	310 2.82	mW mW/°C
Operating Junction Temperature	TJ	135	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

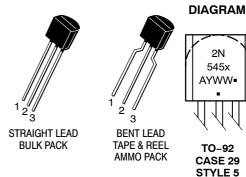
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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**MARKING** 

2N545x = Device Code

x = 7 or 8

A = Assembly Location

Y = Year
WW = Work Week
■ = Pb-Free Package
(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping
2N5457	TO-92	1000 Units/Box
2N5457G	TO-92 (Pb-Free)	1000 Units/Box
2N5458	TO-92	1000 Units/Box
2N5458G	TO-92 (Pb-Free)	1000 Units/Box

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### 2N5457, 2N5458

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			1		I	L
Gate – Source Breakdown Voltage (I <sub>G</sub> = −10 μAdc, V <sub>DS</sub> = 0)		V <sub>(BR)</sub> GSS	-25	_	_	Vdc
Gate Reverse Current $ (V_{GS} = -15 \text{ Vdc}, V_{DS} = 0) $ $ (V_{GS} = -15 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C}) $		l <sub>GSS</sub>	- -	- -	- 1.0 -200	nAdc
Gate-Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, i <sub>D</sub> = 10 nAdc)	2N5457 2N5458	V <sub>GS(off)</sub>	-0.5 -1.0	- -	-6.0 -7.0	Vdc
Gate-Source Voltage $(V_{DS} = 15 \text{ Vdc}, i_D = 100 \mu\text{Adc})$ $(V_{DS} = 15 \text{ Vdc}, i_D = 200 \mu\text{Adc})$	2N5457 2N5458	V <sub>GS</sub>	_ _	-2.5 -3.5	- -	Vdc
ON CHARACTERISTICS			•			
Zero-Gate-Voltage Drain Current (Note 1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	2N5457 2N5458	I <sub>DSS</sub>	1.0 2.0	3.0 6.0	5.0 9.0	mAdc
DYNAMIC CHARACTERISTICS						
Forward Transfer Admittance (Note 1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1 kHz)	2N5457 2N5458	Y <sub>fs</sub>	1000 1500	3000 4000	5000 5500	μmhos
Output Admittance Common Source (Note 1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1 kHz)		Y <sub>os</sub>	-	10	50	μmhos
Input Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1 kHz)		C <sub>iss</sub>	-	4.5	7.0	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1 kHz)		C <sub>rss</sub>	-	1.5	3.0	pF

Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

#### TYPICAL CHARACTERISTICS For 2N5457 Only

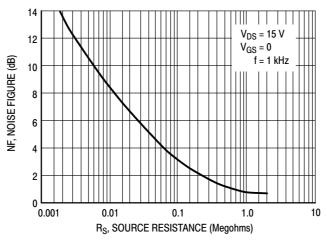


Figure 1. Noise Figure versus Source Resistance

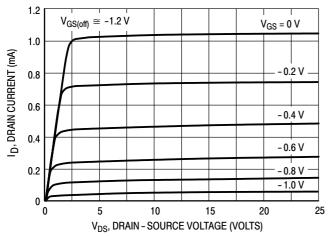


Figure 2. Typical Drain Characteristics

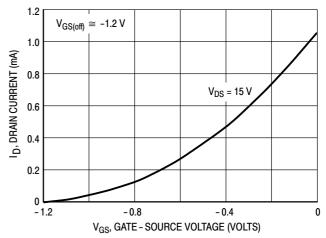


Figure 3. Common Source Transfer Characteristics

#### TYPICAL CHARACTERISTICS For 2N5457 Only

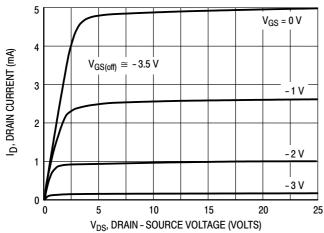


Figure 4. Typical Drain Characteristics

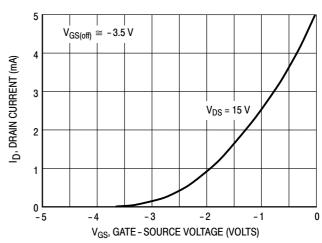


Figure 5. Common Source Transfer Characteristics

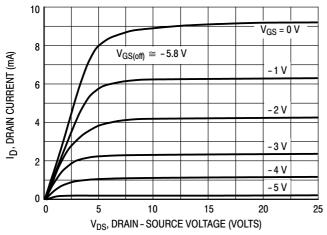


Figure 6. Typical Drain Characteristics

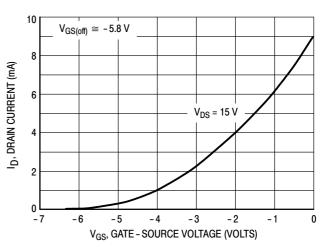
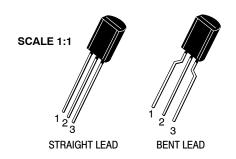


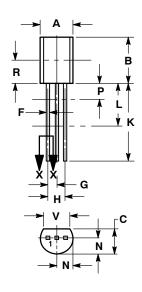
Figure 7. Common Source Transfer Characteristics

NOTE: Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher  $I_{DSS}$  units reduces  $I_{DSS}$ .



TO-92 (TO-226) 1 WATT CASE 29-10 **ISSUE A** 

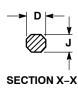
**DATE 08 MAY 2012** 



#### STRAIGHT LEAD







#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 714.5M, 1994.
  CONTROLLING DIMENSION: INCHES.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS
  UNCONTROLLED.
- UNIONI HOLLEU, DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L DIMENSIONS D AND J APPLY BETWEEN DI-MENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: INCHES.
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	INC	HES	MILLIN	ETERS	
DIM	MIN MAX		MIN	MAX	
Α	0.175	0.205	4.44	5.21	
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G	0.094	0.102	2.40	2.80	
J	0.018	0.024	0.46	0.61	
K	0.500		12.70		
N	0.080	0.105 2.		2.66	
P		0.100		2.54	
R	0.135		3.43		
٧	0.135		3.43		

#### **STYLES ON PAGE 2**

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SEATING PLANE

# **TO-92 (TO-226) 1 WATT** CASE 29-10

ISSUE A

#### DATE 08 MAY 2012

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE ANODE
2.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
PIN 1. 2.	ANODE	PIN 1.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
PINI 1	COLLECTOR EMITTER BASE	PIN 1.	SOURCE	PIN 1.	GATE	PIN 1. 2.	EMITTER	PIN 1. 2.	MT 1
	V <sub>CC</sub> GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	2.	CATHODE ANODE GATE	2.	NOT CONNECTED ANODE CATHODE	2.	DRAIN GATE SOURCE
PIN 1. 2.	GATE DRAIN SOURCE	PIN 1.	BASE	PIN 1. 2.	RETURN INPUT OUTPUT	PIN 1. 2.	INPUT GROUND LOGIC		

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